

PMD4003K

MOSFET driver

Rev. 01 — 3 November 2006

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor and high-speed switching diode to protect the base-emitter junction in reverse direction in a SOT346 (SC-59A/TO-236) small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low V_{CEsat} (BISS) transistor and high-speed switching diode as driver
- High-speed switching diode to protect the base-emitter junction
- Application-optimized pinout
- Internal connections to minimize layout effort
- Space-saving solution
- Reduces component count

1.3 Applications

- Power MOSFET driver

1.4 Quick reference data

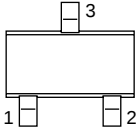
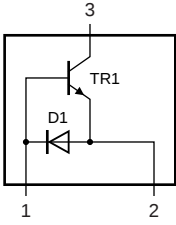
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
NPN transistor						
V_{CEO}	collector-emitter voltage	open base	-	-	40	V
I_C	collector current		-	-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	2	A
Diode						
I_F	forward current		-	-	-0.2	A
V_F	forward voltage	$I_F = -200$ mA	[1] -	-	-1.1	V

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	base TR1, cathode D1		
2	emitter TR1, anode D1		
3	collector TR1		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMD4003K	SC-59A	plastic surface-mounted package; 3 leads	SOT346

4. Marking

Table 4. Marking codes

Type number	Marking code
PMD4003K	D3

5. Limiting values

Table 5. Limiting values

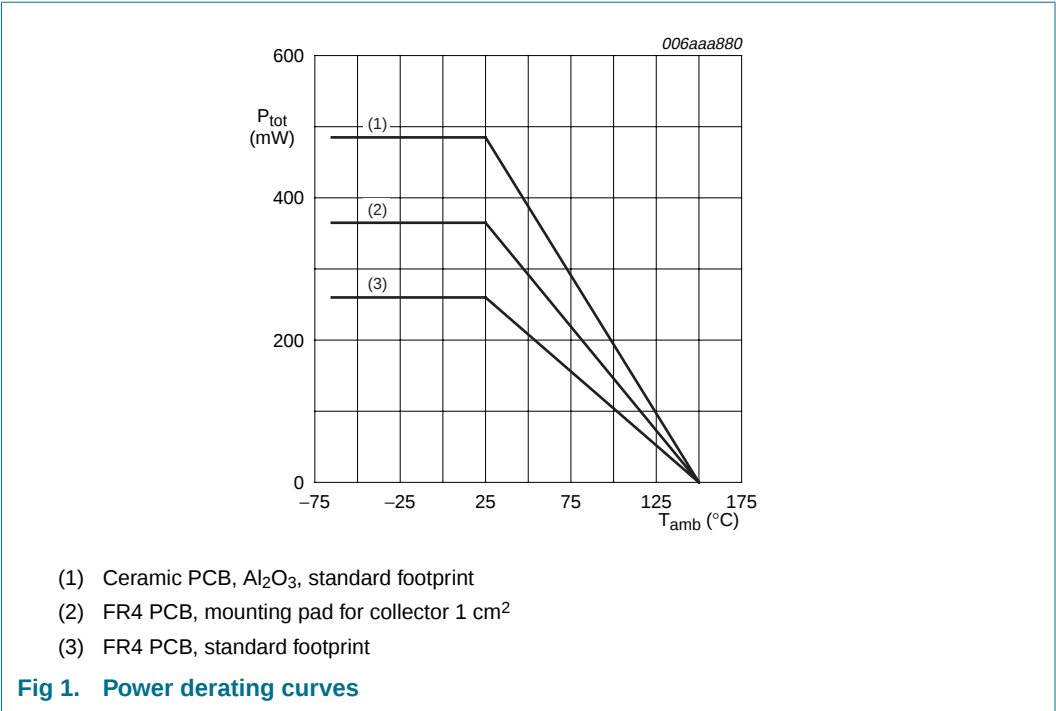
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
NPN transistor					
V _{CBO}	collector-base voltage	open emitter	-	40	V
V _{CEO}	collector-emitter voltage	open base	-	40	V
I _C	collector current		-	1	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	2	A
I _B	base current		-	0.3	A
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	1	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	260	mW
			[2] -	365	mW
			[3] -	485	mW
Diode					
I _F	forward current		-	−0.2	A
I _{FRM}	repetitive peak forward current	t _p ≤ 1 ms; δ = 0.25	-	−0.6	A
I _{FSM}	non-repetitive peak forward current	square wave			
		t _p ≤ 1 μs	-	−9	A
		t _p ≤ 100 μs	-	−3	A
		t _p ≤ 10 ms	-	−1.7	A
Device					
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		−65	+150	°C
T _{stg}	storage temperature		−65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

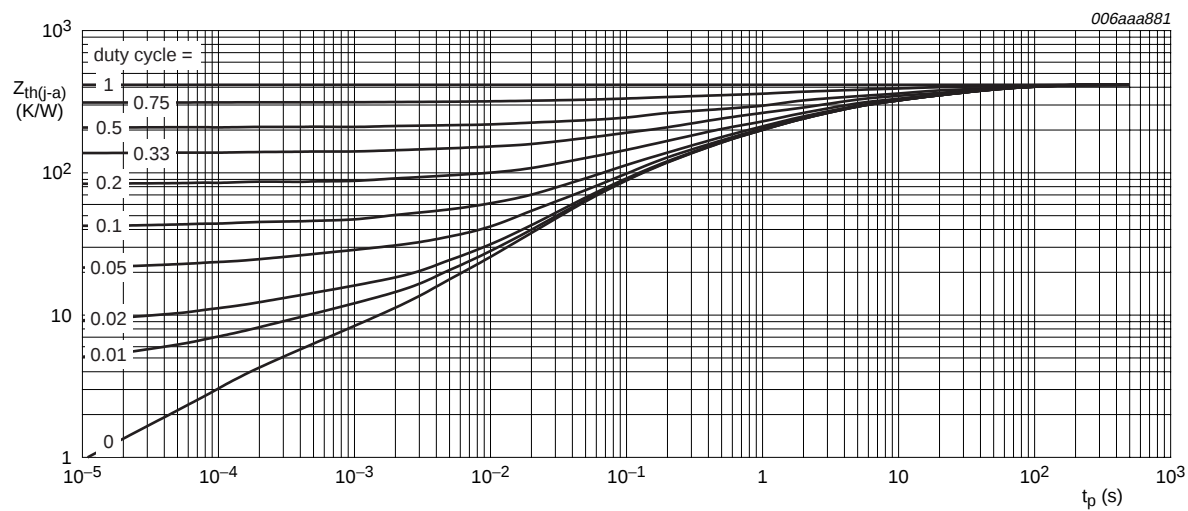


6. Thermal characteristics

Table 6. Thermal characteristics

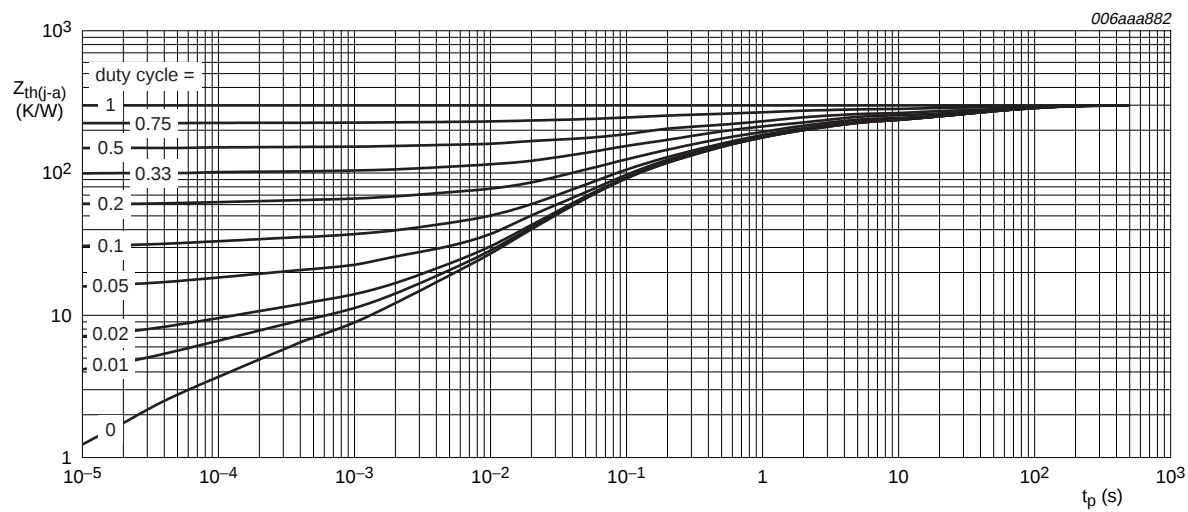
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
NPN transistor						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	480	K/W
			[2]	-	340	K/W
			[3]	-	255	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



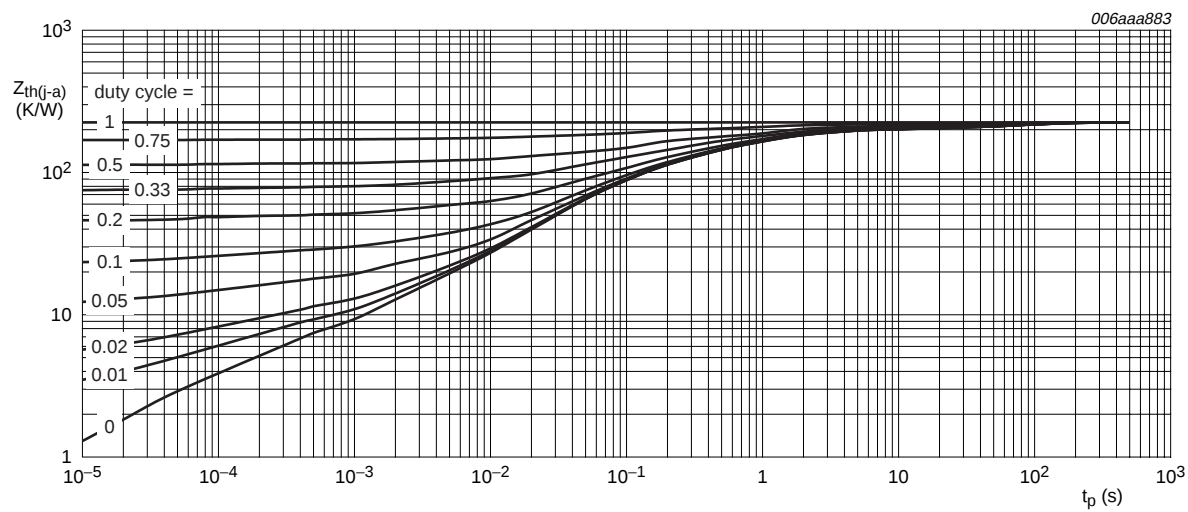
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
NPN transistor						
I _{CBO}	collector-base cut-off current	V _{CB} = 40 V; I _E = 0 A	-	-	100	nA
		V _{CB} = 40 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA	300	450	-	
		V _{CE} = 5 V; I _C = 200 mA	300	450	830	
		V _{CE} = 5 V; I _C = 500 mA	[1] 300	400	-	
		V _{CE} = 5 V; I _C = 1 A	[1] 200	340	-	
		V _{CE} = 5 V; I _C = 2 A	[1] 75	120	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 100 mA; I _B = 5 mA	-	30	80	mV
		I _C = 500 mA; I _B = 50 mA	[1] -	100	120	mV
		I _C = 1 A; I _B = 100 mA	[1] -	180	230	mV
		I _C = 2 A; I _B = 200 mA	[1] -	360	440	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 100 mA; I _B = 5 mA	-	0.75	0.9	V
		I _C = 500 mA; I _B = 50 mA	[1] -	0.9	1.1	V
		I _C = 1 A; I _B = 100 mA	[1] -	1	2	V
		I _C = 2 A; I _B = 200 mA	[1] -	1.1	1.3	V
V _{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 500 mA	[1] -	760	-	mV
Diode						
V _F	forward voltage	I _F = −200 mA	[1] -	-	−1.1	V
Device						
t _d	delay time	I _C = 0.5 A; I _B = 25 mA	-	5	-	ns
t _r	rise time		-	27	-	ns
t _{on}	turn-on time		-	32	-	ns
t _s	storage time		-	1520	-	ns
t _f	fall time		-	184	-	ns
t _{off}	turn-off time		-	1704	-	ns
Device with optional capacitor C1						
t _d	delay time	I _C = 0.5 A; I _B = 25 mA; C1 = 2.2 nF	-	2	-	ns
t _r	rise time		-	2	-	ns
t _{on}	turn-on time		-	4	-	ns
t _s	storage time		-	150	-	ns
t _f	fall time		-	154	-	ns
t _{off}	turn-off time		-	304	-	ns

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

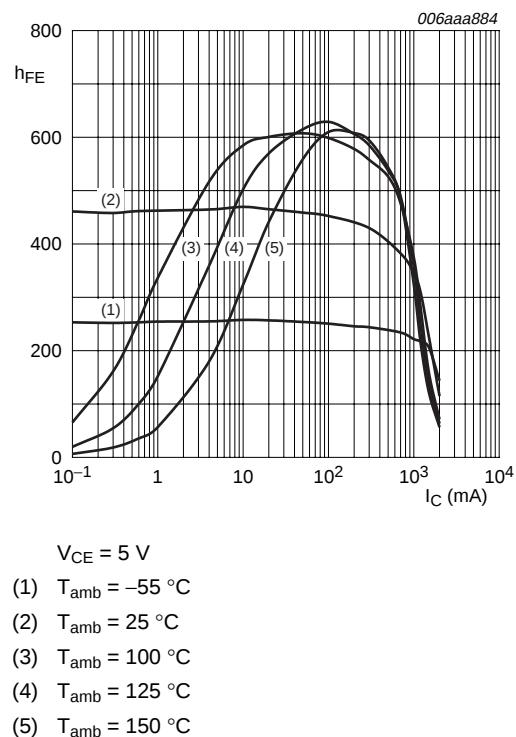


Fig 5. DC current gain as a function of collector current; typical values

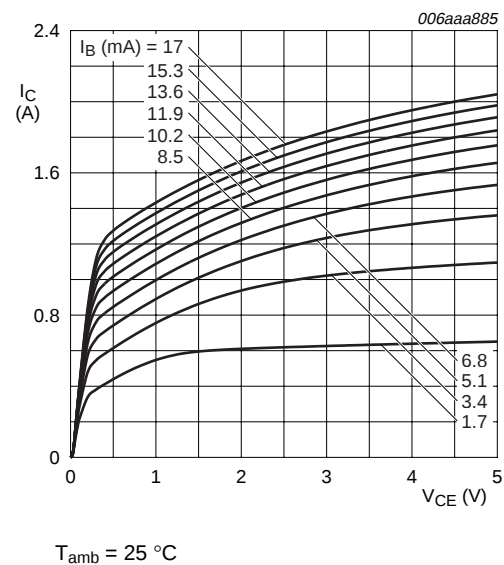


Fig 6. Collector current as a function of collector-emitter voltage; typical values

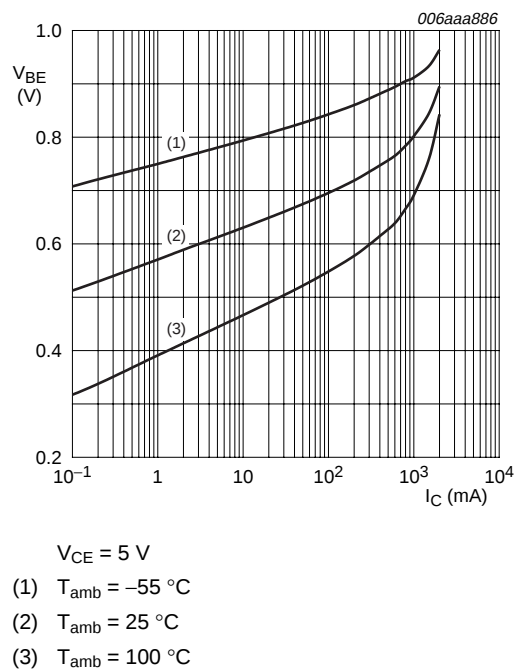


Fig 7. Base-emitter voltage as a function of collector current; typical values

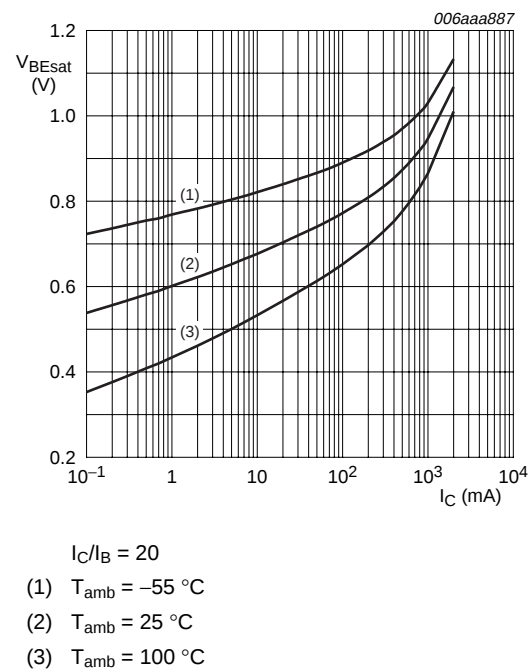
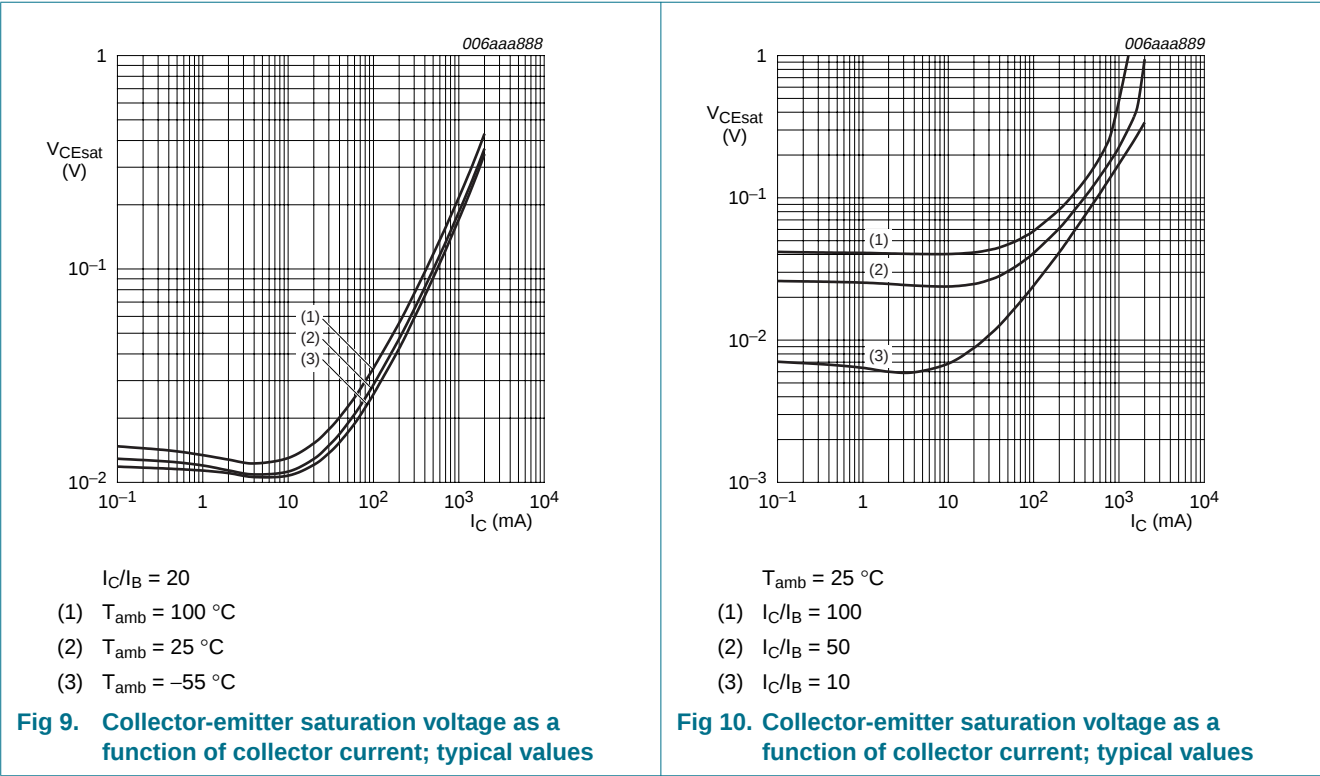
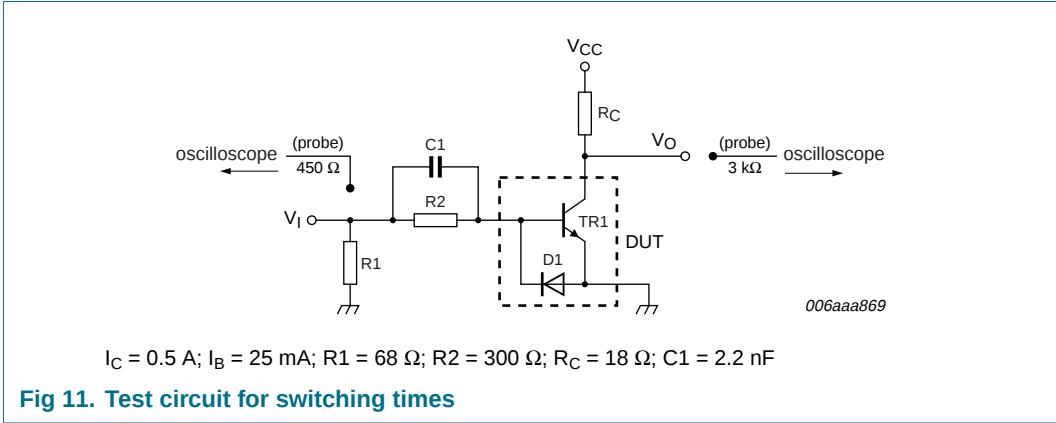


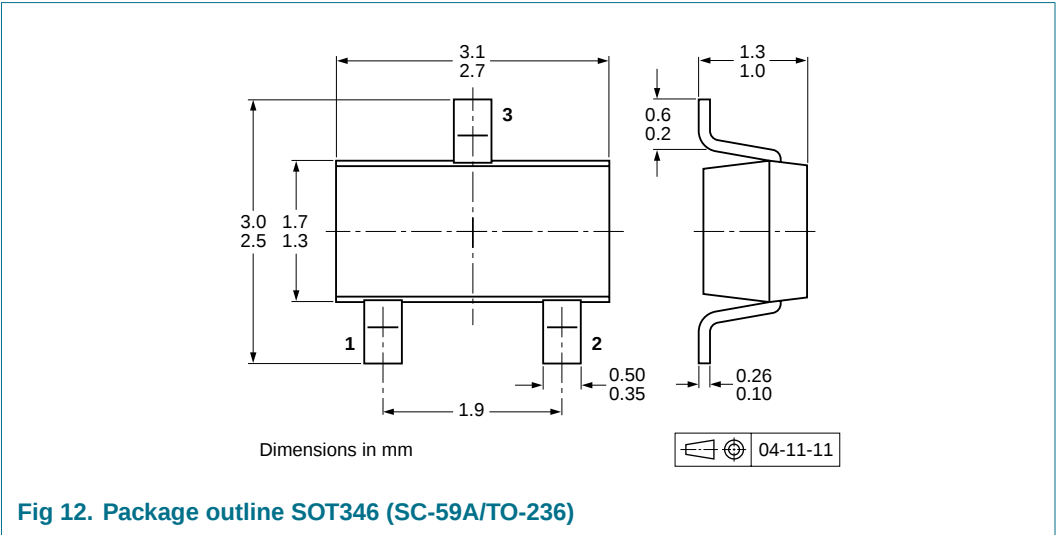
Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



8. Test information



9. Package outline



10. Packing information

Table 8. Packing methods				
The indicated -xxx are the last three digits of the 12NC ordering code. ^[1]				
Type number	Package	Description	Packing quantity	
			3000	10000
PMD4003K	SOT346	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see [Section 15](#).

11. Soldering

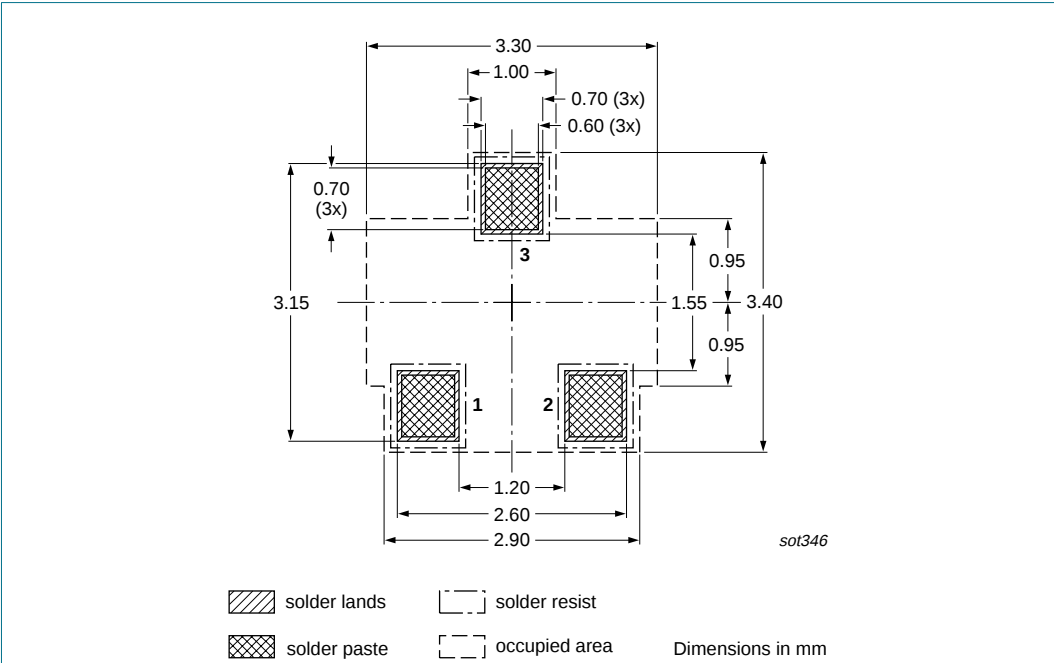


Fig 13. Reflow soldering footprint

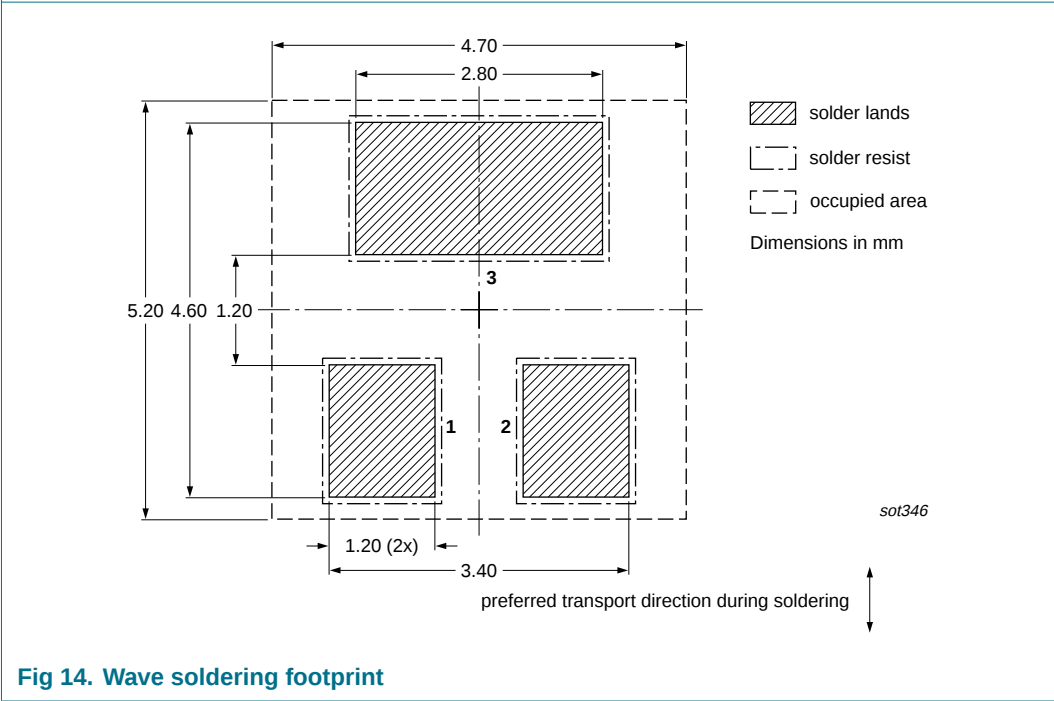
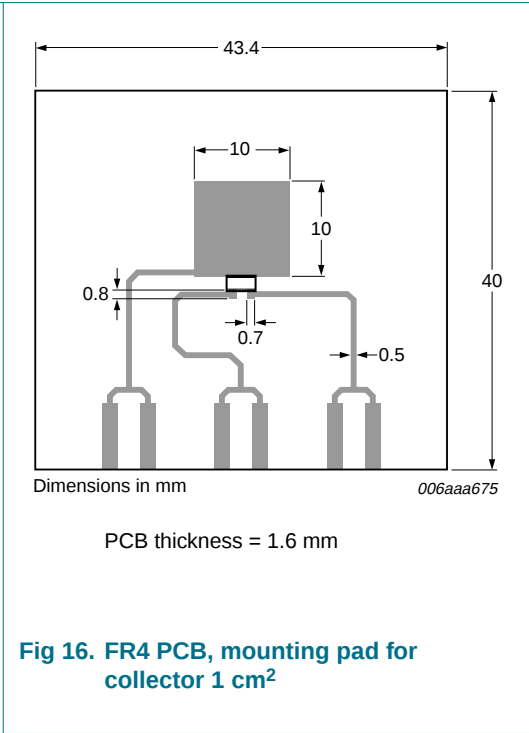
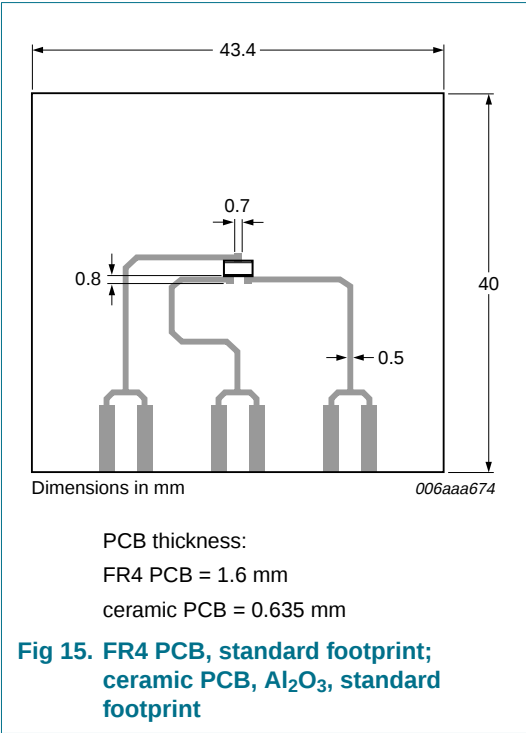


Fig 14. Wave soldering footprint

12. Mounting



13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMD4003K_1	20061103	Product data sheet	-	-

14. Legal information

14.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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